



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Toshihiro ANDO et al.**

Group Art Unit: 1765

Serial No.: 09/926,188

Examiner: **Matthew J. Song**

Filed: **September 20, 2001**

P.T.O. Confirmation No.: 4371

For: **N-TYPE SEMICONDUCTOR DIAMOND AND METHOD OF ITS MAKING**

AMENDMENT UNDER 37 C.F.R. §1.111

Commissioner for Patents
Washington, D.C. 20231

January 7, 2003

Sir:

In response to the Office Action dated October 7, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please amend the paragraph beginning on page 8, line 18 as follows:

Fig.12 (a) shows a secondary electron microscopic (SEM) image of crystallinity of sulfur-doped, n-type semiconductor diamond of the embodiment illustrated;

Fig. 12(b) shows a reflection electron diffraction (RHEED) pattern of crystallinity of sulfur-doped, n-type semiconductor diamond of the embodiment illustrated ; and

IN THE CLAIMS:

Please cancel claim 5 without prejudice or disclaimer.

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